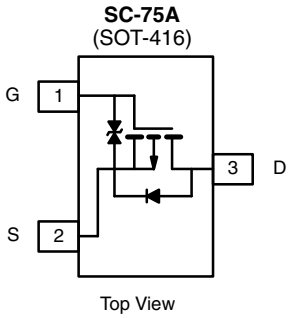
P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS(min.)}$ (V)	$R_{DS(on)}$ (Ω)	$V_{GS(th)}$ (V)	I_D (mA)
- 60	4.0 at V_{GS} = - 10 V	- 1 to 3.0	- 190



Marking Code: F

Ordering Information: Si1021R-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFETs
- High-Side Switching
- Low On-Resistance: 4 Ω
- Low Threshold: - 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Miniature Package
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid-State Relays

BENEFITS

- Ease in Driving Switches
- Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Easily Driven without Buffer
- Small Board Area

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 190	mA
	T_A = 85 °C		- 135	
Pulsed Drain Current[b]		I_{DM}	- 650	
Power Dissipation[a]	T_A = 25 °C	P_D	250	mW
	T_A = 85 °C		130	
Maximum Junction-to-Ambient[a]		R_{thJA}	500	°C/W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

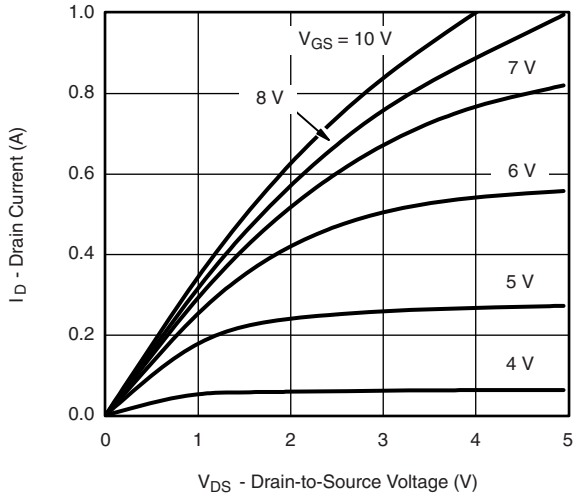
Notes:
a. Surface mounted on FR4 board.
b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 10 µA	- 60			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 0.25 mA	- 1		- 3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 10	µA
		V_{DS} = 0 V, V_{GS} = ± 10 V			± 200	nA
		V_{DS} = 0 V, V_{GS} = ± 10 V, T_J = 85 °C			± 500	
		V_{DS} = 0 V, V_{GS} = ± 5 V			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 50 V, V_{GS} = 0 V			- 25	
		V_{DS} = - 50 V, V_{GS} = 0 V, T_J = 85 °C			- 250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = -10 V, V_{GS} = - 4.5 V	- 50			mA
		V_{DS} = -10 V, V_{GS} = - 10 V	- 600			
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 25 mA			8	Ω
		V_{GS} = - 10 V, I_D = - 500 mA			4	
		V_{GS} = - 10 V, I_D = - 500 mA, T_J = 125 °C			6	
Forward Transconductance	g_{fs}	V_{DS} = - 10 V, I_D = - 100 mA	80			mS
Diode Forward Voltage[a]	V_{SD}	V_{DS} = - 200 mA, V_{GS} = 0 V	80			V
Dynamic						
Total Gate Charge	Q_g	V_{DS} = - 30 V, V_{GS} = - 15 V, $I_D \cong$ - 500 mA		1.7		nC
Gate-Source Charge	Q_{gs}			0.26		
Gate-Drain Charge	Q_{gd}			0.46		
Input Capacitance	C_{iss}	V_{DS} = - 25 V, V_{GS} = 0 V, f = 1 MHz		23		pF
Output Capacitance	C_{oss}			10		
Reverse Transfer Capacitance	C_{rss}			5		
Switching[b]						
Turn-On Time	t_{ON}	V_{DD} = - 25 V, R_L = 150 Ω, $I_D \cong$ - 200 mA, V_{GEN} = - 10 V, R_g = 10 Ω		20		ns
Turn-Off Time	t_{OFF}			35		

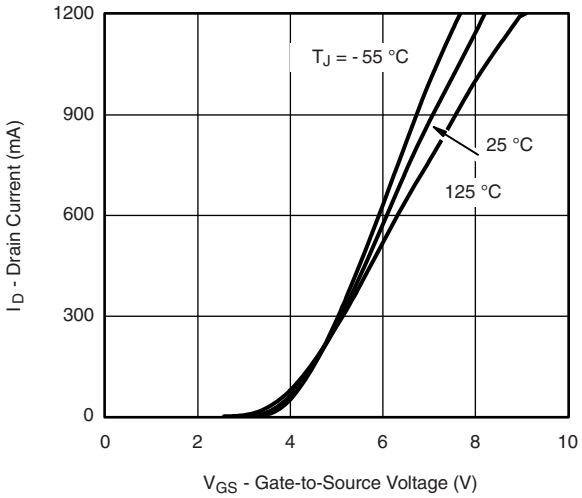
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

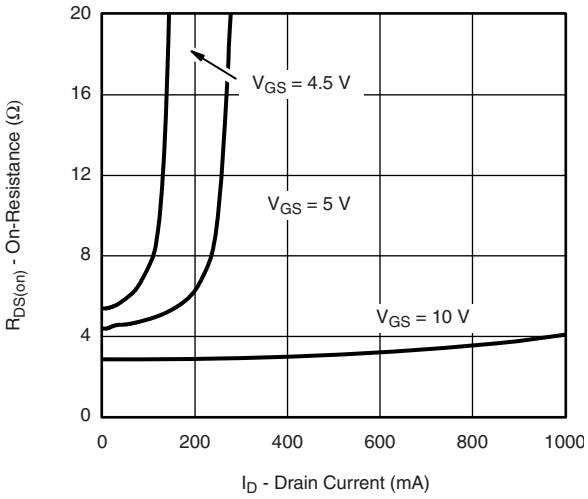
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



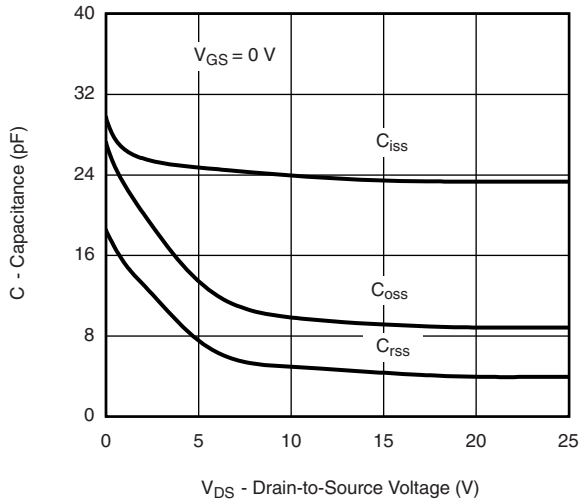
Output Characteristics



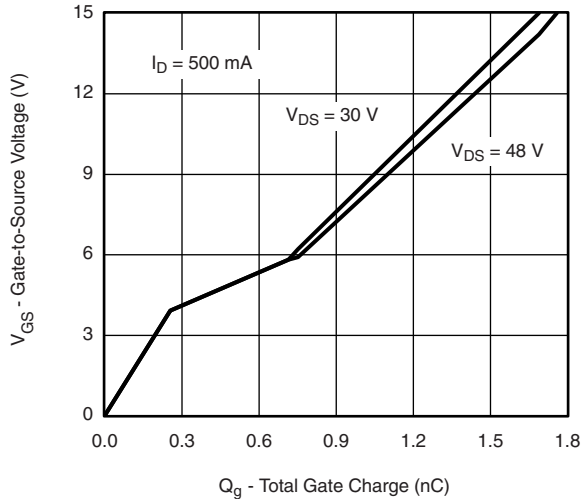
Transfer Characteristics



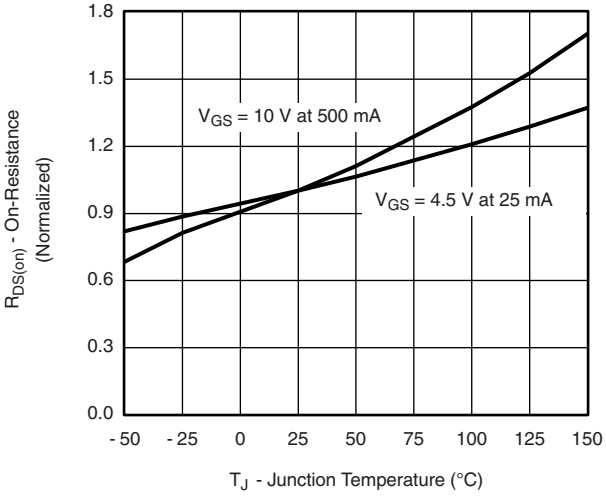
On-Resistance vs. Drain Current



Capacitance

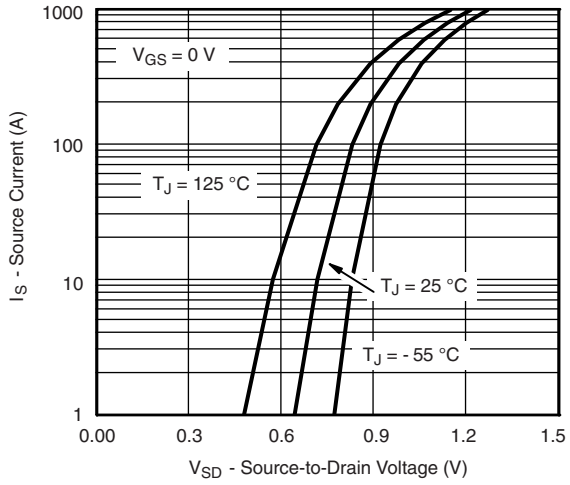


Gate Charge

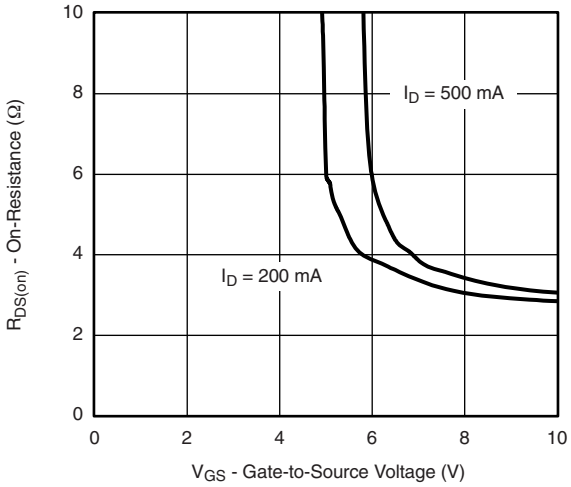


On-Resistance vs. Junction Temperature

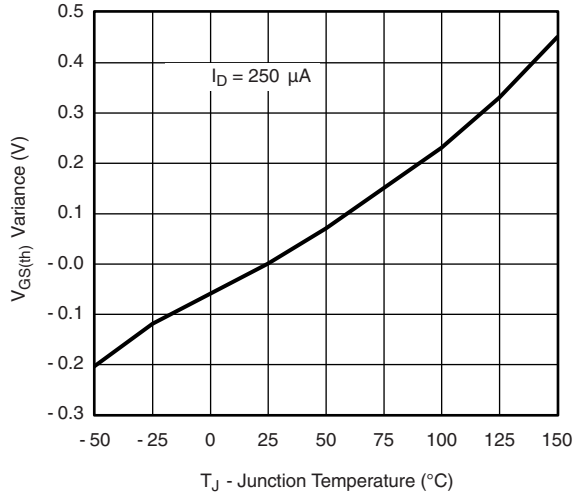
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



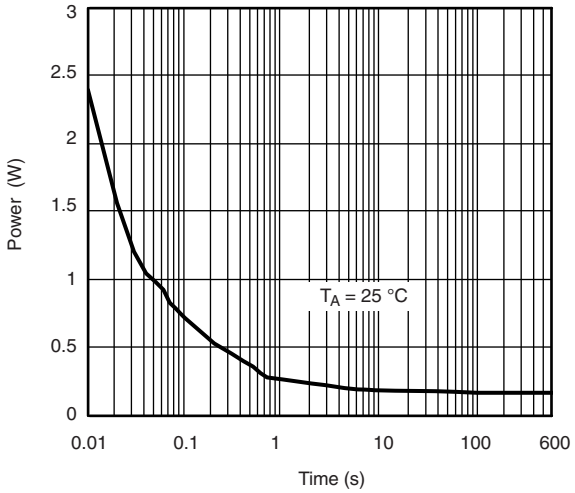
Source-Drain Diode Forward Voltage



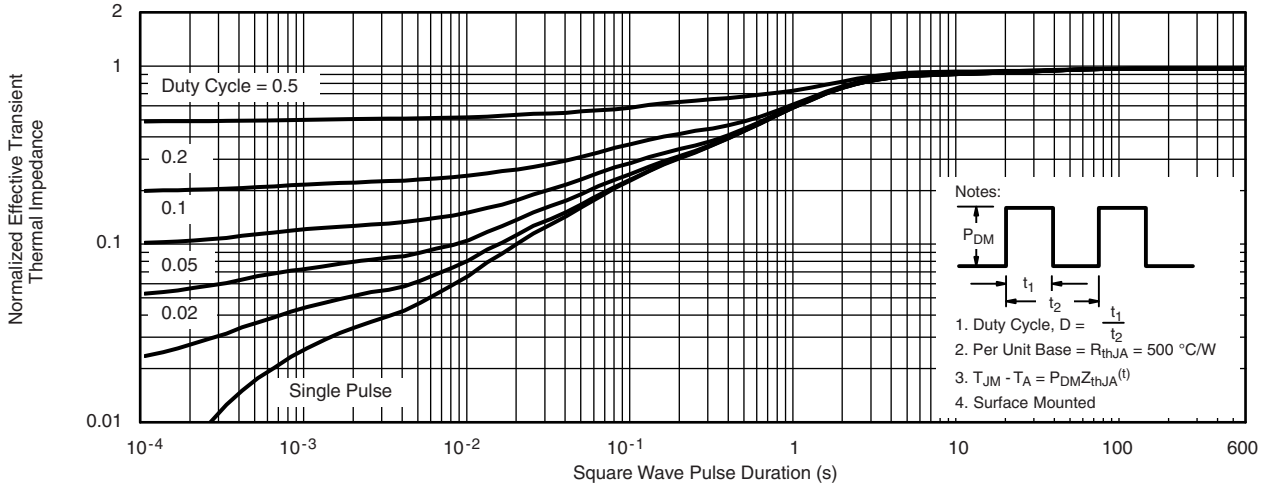
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature



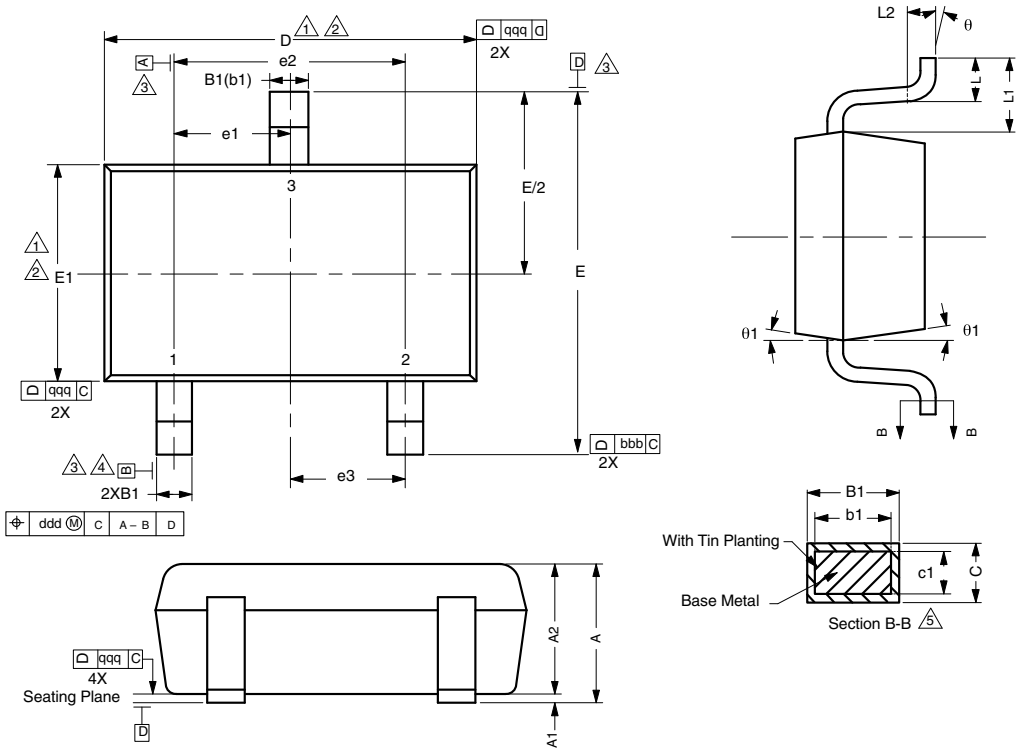
Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

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SC-75A: 3 Leads



DWG: 5868

Notes

Dimensions in millimeters will govern.

1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
3. Datums A, B and D to be determined 0.10 mm from the lead tip.
4. Terminal positions are shown for reference only.
5. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

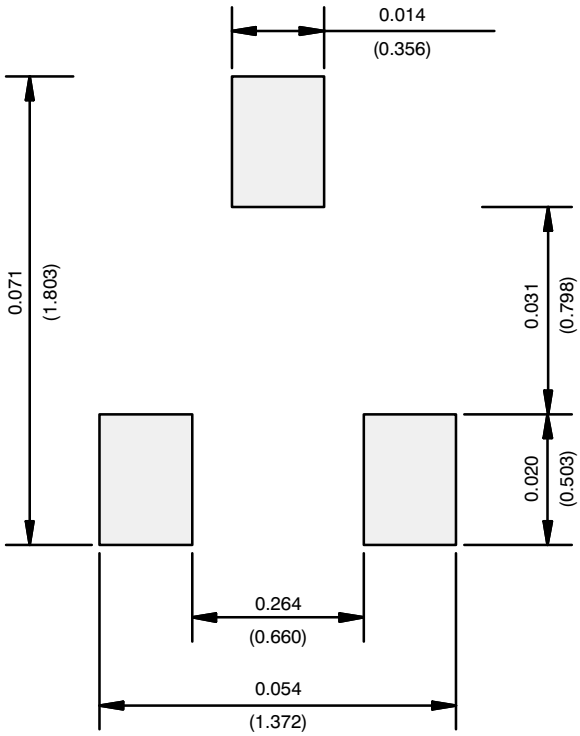
DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.10

DIM.	MILLIMETERS			NOTE
	MIN.	NOM.	MAX.	
A	-	-	0.80	
A1	0.00	-	0.10	
A2	0.65	0.70	0.80	
B1	0.19	-	0.24	5
b1	0.17	-	0.21	
c	0.13	-	0.15	5
c1	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E1	0.66	0.76	0.86	1, 2
e1	0.50 BSC			
e2	1.00 BSC			
e3	0.50 BSC			
L	0.15	0.205	0.30	
L1	0.40 ref.			
L2	0.15 BSC			
q	0°	-	8°	
q1	4°	-	10°	

For technical questions, contact: pmostechsupport@vishay.com

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RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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APPLICATION NOTE

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